

### **Description**

This two-bit non-inverting translator which is a bidirectional voltage-level translator and can be used to build digital switching compatibility between multi voltage systems. This IC uses two separate configurable power supply tracks that including.A ports supporting operating voltages from 1.65 V to 3.6 V with tracking  $V_{\text{CCA}}$  supply, and also including B ports supporting operating voltages from 2.3 V to 5.5V with tracking  $V_{\text{CCB}}$  supply.

The advantage above provides the support of both lower and higher logic signal levels while providing bidirectional translation capabilities between any of the 1.8V,2.5V,3.3V,and 5V voltage circuit points. Placing output-enable(OE) input to low level,all I/Os are forced to high-impedance state that significantly lower the quiescent current consumption. In order to ensure the high-impedance state during power up or power down, OE pin should be tied to GND via a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

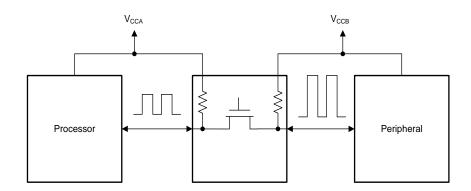
#### **Features**

- · No direction-control
- Data rates24 Mbps (Push Pull)2 Mbps (Open Drain)
- 1.65V to 3.6V on A port and 2.3V to 5.5V on B port (VCCA ≤ VCCB)
- VCC isolation feature:If either VCC input is at GND,both ports are in the high-impedance state
- No power-supply sequencing required:
   either VCCA or VCCB can be ramped first
- · IOFF supports partial-power-down mode operation
- · Operating temperature range:-40°C to +85°C

### **Applications**

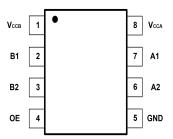
- Handset/Smartphone
- · MART
- · IPC
- · GPIO

### **Circuit Diagram**





### **Pin Assignment**



## BCT0102EDA-TR (SOT-23-8L) Package

## **Device Summary, Pin and Packages (Continued)**

Pin		I/O	Function
Name	YH8		Tunction
VCCB	1	-	B Port Supply Voltage. 2.3V≤Vccв.≤5.5V
B1	2	I/O	Input/Output B1. Referenced to VCCB.
B2	3	I/O	Input/Output B2. Referenced to VCCB.
OE	4	I	Output Enable (Active High).Pull OE low to place all outputs in 3-state mode. Referenced to Vcca.
GND	5	-	Ground
A2	6	I/O	Input/Output A2. Referenced to VCCA.
A1	7	I/O	Input/Output A1. Referenced to VCCA.
VCCA	8	-	A Port Supply Voltage. 1.65V≤VCCA.≤3.6V and VCCA.≤VCCB.

<sup>\*</sup>It is suggested to leave the unconnected pins floating.



### **Order Information**

Package	Orderable Device	Packing Qty	Body Size
SOT-23-8L	BCT0102EDA-TR	Tape and Reel,3000	2.92mm x 2.80mm

### **Absolute Maximum Ratings**

Parameters	Min	Max	Unit			
Supply voltage, Vcca		-0.3	6.0	V		
Supply voltage, Vcсв		-0.3	6.0	V		
land to the second V	A port	-0.3	6.0			
Input voltage range,V <sub>I</sub>	B port	-0.3	6.0	V		
Voltage range applied to any output in the high-impedance or	A port	-0.3	6.0	V		
power-off state, Vo	B port	-0.3	6.0	V		
Voltage range applied to any output in the high or law state. Vo	A port	-0.3	V <sub>CCA</sub> +0.3	V		
Voltage range applied to any output in the high or low state, Vo	B port	-0.3	V <sub>CCA</sub> +0.3	V		
Input clamp current,I <sub>IK</sub>	V <sub>I</sub> <0		-50	mA		
Output clamp current,l <sub>ok</sub>	<b>V</b> <sub>0</sub> <0		-50	mA		
Continuous output current, lo			±50	mA		
Continuous current through Vcca, VccB or GND	Continuous current through Vcca, VccB or GND					
Maximum junction temperature		150	°C			
Storage temperature range	Storage temperature range					

<sup>(1)</sup>Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

### **ESD Ratings**

	E	SD	Value	Unit
\(\( \( \) \	Human-Body Model (HBM) <sup>(1)</sup>	±5K	V	
V(ESD)	Electrostatic Discharge	Charged-Device Model (CDM)(2)	±2K	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed

<sup>(3)</sup> The value of  $V_{\text{CCA}}$  and  $V_{\text{CCB}}$  are provided in the recommended operating conditions table.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



### 2-Bit Bidirectional Voltage-Level Translator

### **Recommended Operating Conditions**

V<sub>CCI</sub> is the supply voltage associated with the input port.V<sub>CCO</sub> is the supply Voltage associated with the output port.

Parameter		Conditions		Тур	Max	Unit	
Supply voltage <sup>(1)</sup>	$V_{CCA}$		1.65		3.6	V	
Supply voltage \		$V_{CCB}$	2.3		5.5	V	
	A-port I/Os	V <sub>CCA</sub> =1.65 V to 1.95 V V <sub>CCB</sub> =2.3 V to 5.5 V	V <sub>CCI</sub> -0.2		Vccı		
High lovel	A-port //Os	V <sub>CCA</sub> =2.3 V to 3.6 V V <sub>CCB</sub> =2.3 V to 5.5 V	Vcci-0.4		Vccı		
High-level input voltage(Vін)	B-nort I/Os	V <sub>CCA</sub> =1.65 V to 3.6V V <sub>CCB</sub> =2.3 V to 5.5 V	V <sub>CCI</sub> -0.4		Vccı	V	
	OE input	V <sub>CCA</sub> =1.65 V to 3.6 V V <sub>CCB</sub> =2.3 V to 5.5 V	V <sub>CCI</sub> ×0.8		5.5		
Low-level	A-port I/Os	V <sub>CCA</sub> =1.65 V to 1.95 V V <sub>CCB</sub> =2.3 V to 5.5 V	0		0.15	W	
input voltage(VIL) <sup>(2)</sup>	B-port I/Os	V <sub>CCA=</sub> 1.65 V to 3.6 V V <sub>CCB</sub> =2.3 V to 5.5 V	0		0.15	V	
OE	OE input	V <sub>CCA</sub> =1.65 V to 3.6 V V <sub>CCB</sub> =2.3 V to 5.5 V	0		V <sub>CCA</sub> ×0.25	V	
Input transition rice	A-port I/Os	push-pull driving			10		
Input transition rise	B-port I/Os push-pull driving				10	ns/V	
or fall rate(Δt/Δv)	C	Control input			10		
TA Operating free- air temperature		-40		85	°C		

<sup>(1)</sup> V<sub>CCA</sub> must be less than or equal to V<sub>CCB</sub>.

<sup>(2)</sup> The maximum  $V_{IL}$  value is provided to ensure that a valid  $V_{OL}$  is maintained. The  $V_{OL}$  value is  $V_{IL}$  plus the voltage drop across the pass gate transistor.



### 2-Bit Bidirectional Voltage-Level Translator

### **Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted) (1) (2) (3)

Pa	arameter	Conditions	Vcca	Vccв	Temp	Min	Тур	Max	Unit	
V <sub>OHA</sub>	Port A Output High Voltage	$I_{OH}$ =-20 $\mu$ A $V_{IB} \ge V_{CCB} - 0.4V$	1.65V to 3.6V	2.3V to 5.5V	Full	V <sub>CCA</sub> ×0.7			V	
Vola	Port A Output Low Voltage	I <sub>OL</sub> =1mA V <sub>IB</sub> ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V	
V <sub>OHB</sub>	Port B Output High Voltage	I <sub>OH</sub> =−20 μA V <sub>IA</sub> ≥ V <sub>CCA</sub> − 0.4V	1.65V to 3.6V	2.3V to 5.5V	Full	V <sub>CCA</sub> ×0.7			V	
Volb	Port B Output Low Voltage	$I_{OL}$ =1mA $V_{IA} \le 0.15 \text{ V}$	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V	
I <sub>I</sub>	Input Leakage	OE	1.65V to 3.6V	2.3V to 5.5V	+25℃			±1	μΑ	
II	Current	OL	1.030 to 3.00	2.57 10 3.57	Full			±1.5	μ	
		A Ports	0V	0V to 5.5V	+25℃			±0.5		
l <sub>off</sub>	Partial Power	7 T OILO	0,	0 10 0.00	Full			±1	μA	
IOI	Down Current	B Ports	0V to 3.6V	0V	+25℃			±0.5	μ	
			0.100.00		Full			±1		
loz	High-impedance State Output	A or B port	1.65V to 3.6V	2.3V to 5.5V	<b>+25</b> ℃			±0.5	μΑ	
102	Current	OE=0V		2.01 10 0.01	Full			±1	Γ".	
			1.65V to VCCB	2.3v to 5.5V	Full			2.5		
Icca	V <sub>CCA</sub> Supply Current		V <sub>I</sub> =V <sub>O</sub> ₌open I <sub>O</sub> =0	3.6v	0V	Full			2.5	μA
			0v	5.5V	Full			-1		
			1.65V to VCCB	2.3v to 5.5V	Full			10		
Icca	V <sub>CCB</sub> Supply Current	V⊨V <sub>O</sub> =open I <sub>O</sub> =0	3.6v	0V	Full			-1	μA	
			0v	5.5V	Full			1		
CCA + ICCB	Combined Supply Current	V <sub>I</sub> =V <sub>CCI</sub> or GND I <sub>0=</sub> 0	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			13	μA	
Iccza	V <sub>CCA</sub> Supply Current	V <sub>I</sub> =V <sub>CCI</sub> or 0V I <sub>O</sub> =0, OE=0V	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			1	μA	
Іссав	V <sub>CCB</sub> Supply Current	V <sub>I</sub> =V <sub>CCI</sub> or 0V I <sub>O</sub> =0, OE=0V	2.3v to 3.6V	2.3v to 5.5V	Full			1	μA	
Ci	Input Capacitance	OE	3.3V	3.3V	+25℃		2.5		PF	
Cio	Input-to-output Internal	A Port	3.3V	3.3V	+25℃		5		PF	
<b>9</b> 0	Capacitance	B Port	3.3V	3.3V	+25℃		5			

<sup>(1)</sup> V<sub>CCI</sub> is the VCC associated with the input port.

<sup>(2)</sup>  $V_{\text{CCO}}$  is the VCC associated with the output port

<sup>(3)</sup>  $V_{\text{CCA}}$  must be less than or equal to  $V_{\text{CCB}}$ .

### **Timing Requirements**

### $V_{CCA} = 1.8V \pm 0.15V$

		$V_{\text{CCB}}$ =2.5 $V$ $\pm$ 0.2 $V$	$V_{CCB}$ =3.3 $V$ ±0.2 $V$	$V_{\text{CCB}}$ =5 $V$ $\pm$ 0.2 $V$	Unit
		Тур	Тур	Тур	Unit
5 . 5 .	Push-pull Driving	21	22	24	Mbpa
Data Rate	Open-drain Driving	2	2	2	Mbps
Pulse	Push-pull Driving (Data Inputs)	47	45	41	
Duration(tw)	Open-drain Driving (Data Inputs)	500	500	500	ns

### $V_{\text{CCA}}$ =2.5 $V\pm0.15V$

· · · · · · · · · · · · · · · · · · ·		$V_{\text{CCB}}$ =2.5 $V$ $\pm$ 0.2 $V$	$V_{CCB}$ =3.3 $V$ ±0.2 $V$	$V_{\text{CCB}}$ =5 $V$ ±0.2 $V$	Unit
		Тур	Тур	Тур	OIIIL
Data Rate	Push-pull Driving	20	22	24	Mhna
Data Rate	Open-drain Driving	2	2	2	Mbps
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	50	45	41	
	Open-drain Driving (Data Inputs)	500	500	500	ns

### $V_{\text{CCA}}$ =3.3 $V\pm0.15V$

		V <sub>CCB</sub> =3.3V±0.2V	V <sub>CCB</sub> =5V±0.2V	l l m iá
		Тур	Тур	Unit
Data Rate	Push-pull Driving	23	24	Mbps
Data Rate	Open-drain Driving	2	2	Ivibps
Pulso Duration(tu)	Push-pull Driving (Data Inputs)	43	41	no
Pulse Duration(tw)	Open-drain Driving (Data Inputs)	500	500	ns

### Switching Characteristics:Vcc=1.8V±0.15V

over recommended operating free-air temperature range (unless otherwise noted)

	Darameter	Parameter Conditions		V <sub>ccB</sub> =2.5V±0.2V	V <sub>ccB</sub> =3.3V±0.2V	V <sub>ccB</sub> =5V±0.2V	Units
	Parameter		Conditions	Тур	Тур	Тур	Units
t <sub>PHL</sub>	Propagation Delay Time	A to B	Push-pull Driving	5.6	5	5	ns
VPTIL.	High-to-low Output	Atob	Open-drain Driving	7.5	7.9	8.3	110
t <sub>РСН</sub>	Propagation Delay Time	A to B	Push-pull Driving	10.0	9.5	9	ns
(PLH	low-to-high Output	Alob	Open-drain Driving	181	170	154	113
t <sub>PHL</sub>	Propagation Delay Time	B to A	Push-pull Driving	7	7.1	7.2	
	High-to-low Output		Open-drain Driving	7.6	8.1	9.2	ns
t <sub>РLН</sub>	Propagation Delay Time	B to A	Push-pull Driving	7.6	6.9	6	ns
	low-to-high Output		Open-drain Driving	163	145	118	
t <sub>en</sub>	Enable Time		OE to A or B	135	159	182	ns
t <sub>dis</sub>	Disable Time		OE to A or B	170	174	181	ns
	Input Diag Time	A port	Push-pull Driving	13.4	11.9	10.6	
t <sub>rA</sub>	Input Rise Time	rise time	Open-drain Driving	68	66	62	ns
t <sub>rB</sub>	Input Rise Time	B port	Push-pull Driving	13	12	11.6	ns
чв	inputitise fille	rise time	Open-drain Driving	66	65	50	116
t <sub>fA</sub>	Input Fall Time	A port fall	Push-pull Driving	5.6	4.7	4.0	ns
чА	input i all Time	time	Open-drain Driving	5.0	5.1	5.2	116
t <sub>nB</sub>	Input Fall Time	B port fall	Push-pull Driving	3.0	3.0	2.9	ns
чь	mpacran rine	time	Open-drain Driving	6.1	5.6	4.4	
tsk(o)	Skew(time), Output	Cha	annel-to-Channel Skew	0.5	0.5	0.5	ns
Maximum Data Rate			Push-pull Driving	22	23	24	Mb
		Open-drain Driving		2	2	2	Mbps



### Switching Characteristics:Vcc=2.5V±0.15V

over operating free-air temperature range (unless otherwise noted)

	Parameter	Conditions		V <sub>ccB</sub> =2.5V±0.2V	V <sub>ccB</sub> =3.3V±0.2V	V <sub>ccB</sub> =5V±0.2V	Units	
	Parameter		Conditions	Тур	Тур	Тур	Units	
<b>t</b>	Propagation Delay Time	A to B	Push-pull Driving	3.5	3.5	3.2	no	
tpHL	High-to-low Output	AIOB	Open-drain Driving	6.3	6.5	6.7	ns	
	Propagation Delay Time		Push-pull Driving	4.5	4.9	4.7		
tрцн	low-ťo-high Output	A to B	Open-drain Driving	158	152	142	ns	
tрнL	Propagation Delay Time	B to A	Push-pull Driving	3.7	3.9	4.6		
PHL	High-to-low Output	BIOA	Open-drain Driving	6	6.6	7.7	ns	
tрцн	Propagation Delay Time	B to A	Push-pull Driving	4.8	4	2.5	ns	
YLH .	low-to-high Output	DIO A	Open-drain Driving	153	138	116		
t <sub>en</sub>	Enable Time	OE to A or B		7.7	41.8	130	ns	
t <sub>dis</sub>	Disable Time		OE to A or B	175	181	182	ns	
+.	Input Rise Time	A port	Push-pull Driving	9.8	8.6	7.5	ns	
t <sub>rA</sub>	input ruse nine	Rise Time	Open-drain Driving	79	77	65	113	
	Input Rise Time	B port	Push-pull Driving	9.8	8.7	8.1	no	
trB	input Nise fillie	Rise Time	Open-drain Driving	93	68	53	ns	
t <sub>fA</sub>	Input Fall Time	A port Fall	Push-pull Driving	4.6	4.1	3.6		
цА	inputran rine	Time	Open-drain Driving	5.1	5.1	5.2	ns	
t <sub>fB</sub>	Input Fall Time	B port Fall	Push-pull Driving	4.5	4.0	4.0	ns	
LIB .	mputi an time	Time Open-drain Driving		6.9	7.4	7.8	110	
tsĸ(o)	Skew(time), Output	Channel-to-Channel Skew		0.5	0.5	0.5	ns	
Ma	ximum Data Rate		Push-pull Driving	22	24	24	Mbps	
IVIA	Amam Data Nato		Open-drain Driving	2	2	2	ivips	

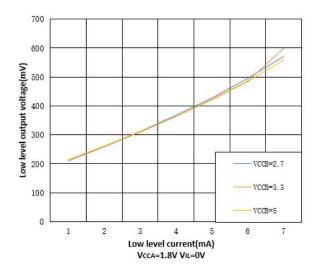


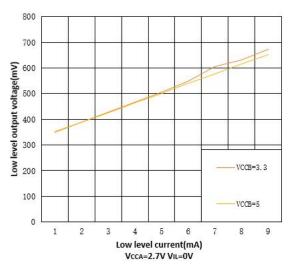
### Switching Characteristics:Vcc=3.3V±0.15V

over recommended operating free-air temperature range (unless otherwise noted)

	Parameter		Conditions	V <sub>ccB</sub> =3.3V±0.2V	V <sub>ccB</sub> =5V±0.2V	Units
	Farameter		Conditions	TYP	TYP	Ullits
tрнL	Propagation Delay Time	A to B	Push-pull Driving	2.1	2.2	ns
PHL	High-to-low Output	Alob	Open-drain Driving	5.9	6.1	115
	Propagation Delay Time	A 4 - D	Push-pull Driving	1	3.3	
t <sub>РLН</sub>	High-to-low Output	A to B	Open-drain Driving	138	131	ns
tрнL	Propagation Delay Time	B to A	Push-pull Driving	2.3	2.6	
PHL	High-to-low Output	BIOA	Open-drain Driving	5.4	6.6	ns
tецн	Propagation delay time	B to A	Push-pull Driving	1.0	1.0	ns
	low-to-high Output		Open-drain Driving	133	115	
t <sub>en</sub>	Enable Time		OE to A or B	4.7	5.2	ns
t <sub>dis</sub>	Disable Time		OE to A or B	174	182	ns
trA	Input Rise Time	A port	Push-pull Driving	7.4	6.6	ns
uA	input Nise Time	Rise Time	Open-drain Driving	75	67	113
t <sub>гВ</sub>	Input Rise Time	B port	Push-pull Driving	7.7	7.1	ns
ив	input ruse rime	Rise Time	Open-drain Driving	70	65	10
t <sub>fA</sub>	Input Fall Time	A port Fall	Push-pull Driving	3.4	3.0	ns
цА	mput raii riine	Time	Open-drain Driving	5.1	5.1	10
tre	Input Fall Time	B port Fall	Push-pull Driving	3.5	3.2	ns
чВ	πρατιαπιπισ	Time	Open-drain Driving	6.8	6.7	110
tsĸ(o)	Skew(time), Output	CI	nannel-to-Channel Skew	0.5	0.5	ns
М	aximum Data Rate		Push-pull Driving	24	24	Mbps
	Waximum Data Nate		Open-drain Driving		2	.F

### **Typical Characteristics**





Low Level Output Voltage vs Low Level Current

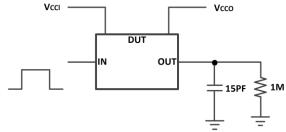
Low Level Output Voltage vs Low Level Current

### **Parameter Measurement Information**

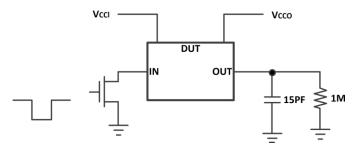
Unless otherwise noted, all input pulsed are supplied by generators having the following characteristics:

- PSRR 10MHz
- Zo=50 Ω
- dv/dt ≥1V/ns

Note: All input pulses are measured one at a time with one transition per measurement

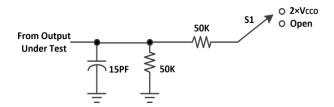


Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using a Push-Pull Driver



Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using an Open-Drain Driver

### **Parameter Measurement Information (Continued)**

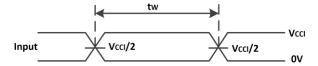


### Load Circuit for Enable/Disable Time Measurement

### Switch Configuration for Enable/Disable Timing

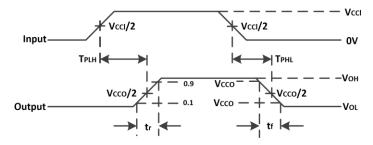
Test	S1
t <sub>PZL</sub> <sup>(1)</sup> , t <sub>PLZ</sub> <sup>(2)</sup>	2×Vcco
t <sub>РНZL</sub> <sup>(1)</sup> , t <sub>РZH</sub> <sup>(2)</sup>	Open

- (1) tPZL and tPZH are the same as ten.
- (2) tPLZ and tPHZ are the same as tdis.

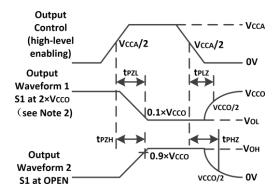


(1) All input pulses are measured one at a time, with one transition per measurement.

#### **Voltage Waveforms Pulse Duration**



#### **Voltage Waveforms Propagation Delay Times**



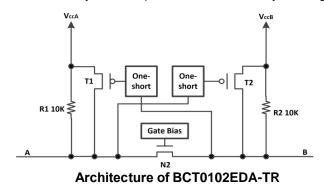
Voltage Waveforms Enable and Disable

#### Overview

The BCT0102EDA-TR IC is a Bi-direction voltage-level translator specifically designed for translating logic voltage levels. The A port can accept I/O voltages that cover from 1.65 V to 3.6 V range; The B port can accept I/O voltages from 2.3V to 5.5 V. The device is a pass-gate architecture with edge-rate accelerators (one-shots) to improve the overall data rate. 10-k $\Omega$  pullup resistors that usually used in open-drain applications have been integrated inside IC with the advantage saving an external resistor. Not only the IC is designed for open-drain applications, but also this device can translate push-pull CMOS logic outputs.

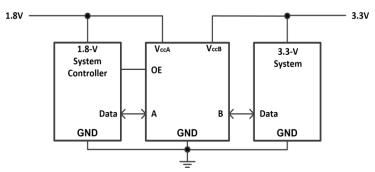
#### **Architecture**

The BCT0102EDA-TR architecture (see Figure below) is a translator with Bi-direction-Sensing function that means a direction-control mechanism to control the direction of data flow from A to B or from B to A is not needed. These two bidirectional channels independently determine the direction of data flow without a direction-control signal. This auto-direction feature is realized by each I/O pin can be automatically reconfigured as either an input or an output.



#### **Application Information**

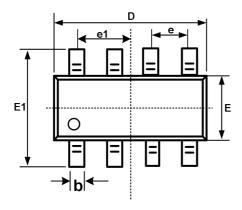
The BCT0102EDA-TR device can be used to bridge the digital-switching compatibility gap between two voltage nodes to successfully interface logic threshold levels found in electronic systems. It should be used in a point-to-point topology for interfacing devices or systems operating at different interface voltages with one another. Its primary target application use is for interfacing with open-drain drivers on the data I/Os such as I2C or 1-wire, where the data is bidirectional and no control signal is available. The device can also be used in applications where a push-pull driver is connected to the data I/Os, but the WTXS0108E might be a better option for such push-pull applications.

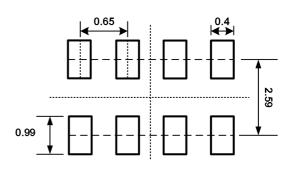


**Typical Application Schematic** 

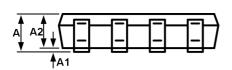


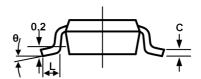
# Package Outline Dimensions SOT-23-8L





Recommended Land Pattern (Unit: mm)





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
А	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.650BSC		0.026BSC	
e1	0.975BSC		0.038BSC	
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



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